	Application No.	Applicant(s)	
Notice of Allowability	10/600,259	LUTZE ET AL.	m
Notice of Allowability	Examiner	Art Unit	
	Thao P. Le	2818	
The MAILING DATE of this communication appe All claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RI of the Office or upon petition by the applicant. See 37 CFR 1.313	(OR REMAINS) CLOSED in or other appropriate commu GHTS. This application is s	this application. If not include inication will be mailed in due of	d course. THIS
1. X This communication is responsive to 4/27/05.	(N)		
2. The allowed claim(s) is/are 1-12, 18 and 13 -> 23	(10)		
3. $igotimes$ The drawings filed on $20 June 2003$ are accepted by the E:	xaminer.		
4. Acknowledgment is made of a claim for foreign priority una a) All b) Some* c) None of the: 1. Certified copies of the priority documents have 2. Certified copies of the priority documents have 3. Copies of the certified copies of the priority documents have International Bureau (PCT Rule 17.2(a)). * Certified copies not received: Applicant has THREE MONTHS FROM THE "MAILING DATE" noted below. Failure to timely comply will result in ABANDONM THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.	been received. been received in Application cuments have been received	n No I in this national stage applicat	
5. A SUBSTITUTE OATH OR DECLARATION must be subm INFORMAL PATENT APPLICATION (PTO-152) which give	es reason(s) why the oath or	AMINER'S AMENDMENT or Note that the control of the	OTICE OF
6. CORRECTED DRAWINGS (as "replacement sheets") mus		// DTO 049) attached	
(a) ☐ including changes required by the Notice of Draftsperson's Patent Drawing Review (PTO-948) attached1) ☐ hereto or 2) ☐ to Paper No./Mail Date			
(b) ☐ including changes required by the attached Examiner's Paper No./Mail Date		in the Office action of	
Identifying indicia such as the application number (see 37 CFR 1 each sheet. Replacement sheet(s) should be labeled as such in t	.84(c)) should be written on the header according to 37 CF	ne drawings in the front (not the R 1.121(d).	back) of
7. DEPOSIT OF and/or INFORMATION about the depo attached Examiner's comment regarding REQUIREMENT	sit of BIOLOGICAL MATE	ERIAL must be submitted. N	lote the
Attachment(s) 1. ☑ Notice of References Cited (PTO-892) 2. ☐ Notice of Draftperson's Patent Drawing Review (PTO-948) 3. ☐ Information Disclosure Statements (PTO-1449 or PTO/SB/O Paper No./Mail Date	6. Interview St Paper No./ 7. Examiner's	formal Patent Application (PTC ummary (PTO-413), Mail Date Amendment/Comment Statement of Reasons for Allo 	

Application/Control Number: 10/600,259 Page 2

Art Unit: 2818

DETAILED ACTION

1. This office action is in response to amendment made on 04/27/05.

Claims 1, 8, and 18 have been amended.

Claims 1-12 and 18-23 are pending.

Reason for allowance

2. Claims 1-12, 18-23 are allowed.

The following is an examiner's statement of reason for allowance:

a) Set of claims 1-12:

None of the references of record teaches or suggests the claimed limitations having a method of making an array of non-volatile memory cells on a semiconductor substrate surface comprising, among other steps cited in independent claim 1, the steps of forming an array of first floating gate portions across the substrate surface with a gate dielectric layer, forming second floating gate portions defined by the sidewall elements and contact the first floating gate portion, and removing the sidewall elements thereby exposing surfaces of the first and second floating gate portions.

b) **Set of claims 18-19:**

None of the references of record teaches or suggests the claimed limitations having a method of making an array of non-volatile memory cells on a semiconductor substrate surface comprising, among other steps cited in independent claim 18, the steps of forming an array of first floating gate portions, forming second floating gate portions extending from first floating gate portions wherein each second floating gate portion extends along a plane

Application/Control Number: 10/600,259 Page 3

Art Unit: 2818

perpendicular to the plane of the substrate surface and wherein the plane of the second floating gate portion bisects the first floating gate portion, and the second floating gate portion being self-aligned to the first floating gate portion.

c) Set of claims 20-23:

None of the references of record teaches or suggests the claimed limitations having a method of forming a non-volatile memory cells on a semiconductor substrate surface comprising, among other steps cited in independent claim 20, the steps of forming a layer of floating gate material extending across the layer of gate dielectric, forming shallow trench isolation structures that divide the layer of floating gate material into strips and extend in one direction, forming spacers along sidewalls of the second masking strips which extending in the second direction wherein the spacers overlying the first floating gate portions, and then forming second floating gate portions by filling gaps between spacers of adjacent second masking strips.

3. Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance".

Application/Control Number: 10/600,259 Page 4

Art Unit: 2818

Conclusion

4. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure.

5. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Thao P. Le whose telephone number is 571-272-1785. The examiner can normally be reached on M-T (7-6).

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, David Nelms can be reached on 571-272-1787. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Thao P. Le Examiner Art Unit 2818